

### Monolithic N-Channel JFET Duals

**SST404      U401**  
**SST406      U404**  
**U406**

### Product Summary

Part Number	V <sub>GS(off)</sub> (V)	V <sub>(BR)GSS</sub> Min (V)	g <sub>fs</sub> Min (mS)	I <sub>G</sub> Typ (pA)	V <sub>GS1</sub> - V <sub>GS2</sub>   Max (mV)
U401	-0.5 to -2.5	-40	1	-2	5
SST/U404	-0.5 to -2.5	-40	1	-2	15
SST/U406	-0.5 to -2.5	-40	1	-2	40

For applications information see AN106, page 28.

### Features

- Monolithic Design
- High Slew Rate
- Low Offset/Drift Voltage
- Low Gate Leakage: 2 pA
- Low Noise
- High CMRR: 102 dB

### Benefits

- Tight Differential Match vs. Current
- Improved Op Amp Speed, Settling Time Accuracy
- Minimum Input Error/Trimming Requirement
- Insignificant Signal Loss/Error Voltage
- High System Sensitivity
- Minimum Error with Large Input Signal

### Applications

- Wideband Differential Amps
- High-Speed, Temp-Compensated, Single-Ended Input Amps
- High-Speed Comparators
- Impedance Converters

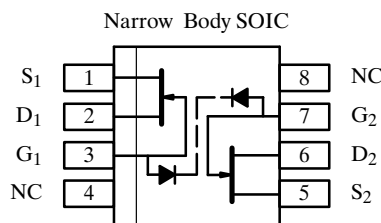
### Description

The SST/U401 series of high-performance monolithic dual JFETs features extremely low noise, tight offset voltage and low drift over temperature specifications, and is targeted for use in a wide range of precision instrumentation applications. This series has a wide selection of offset and drift specifications with the U401 featuring a 5-mV offset and 10-μV/°C drift.

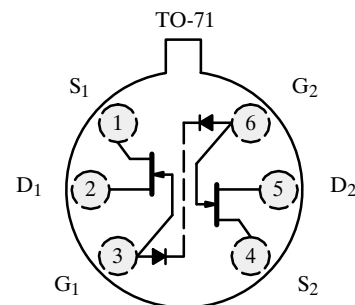
The U series' hermetically sealed TO-71 package is available with full military processing (see Military

Information). The SST series SO-8 package provides ease of manufacturing, and the symmetrical pinout prevents improper orientation. The SO-8 package is available with tape-and-reel options for compatibility with automatic assembly methods (see Packaging Information).

For similar high-gain products in TO-78 packaging, see the 2N5911/5912 data sheet.



Top View  
SST404, SST406



Top View  
U401, U404, U406

### Absolute Maximum Ratings

Gate-Drain, Gate-Source Voltage	-40 V
Gate Current	10 mA
Lead Temperature (1/16" from case for 10 sec.)	300°C
Storage Temperature: U Prefix	-65 to 200°C
SST Prefix	-55 to 150°C
Operating Junction Temperature	-55 to 150°C

Power Dissipation: Per Side <sup>a</sup>	300 mW
Total <sup>b</sup>	500 mW

- Notes
- Derate 2.4 mW/°C above 25°C
  - Derate 4 mW/°C above 25°C

### Specifications<sup>a</sup>

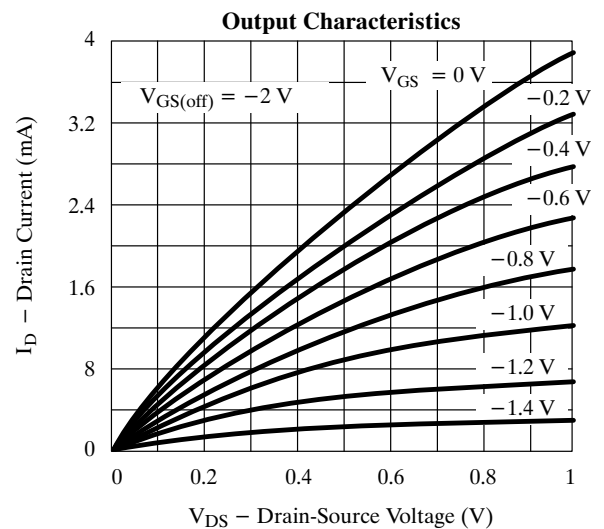
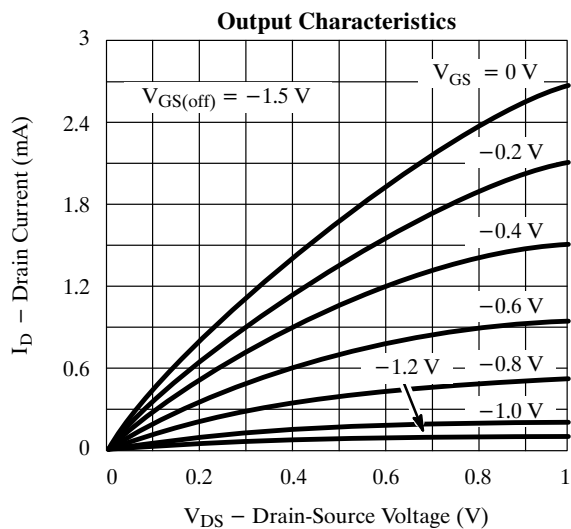
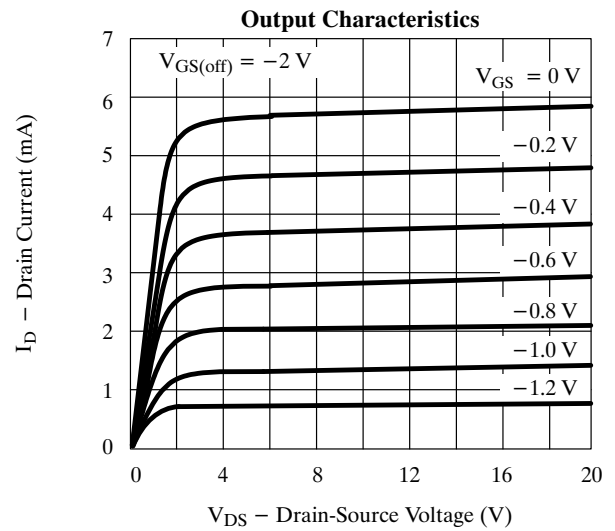
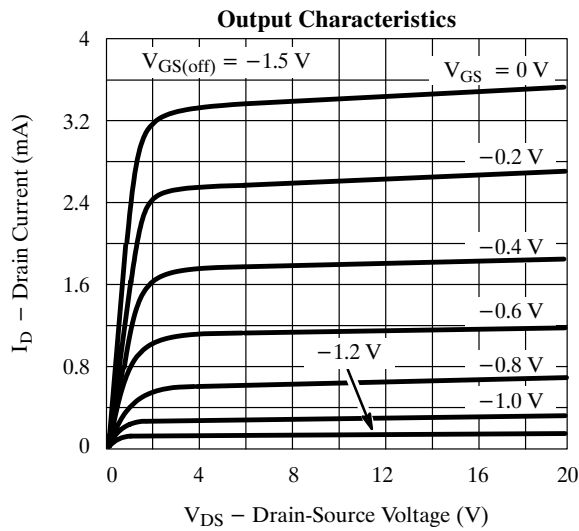
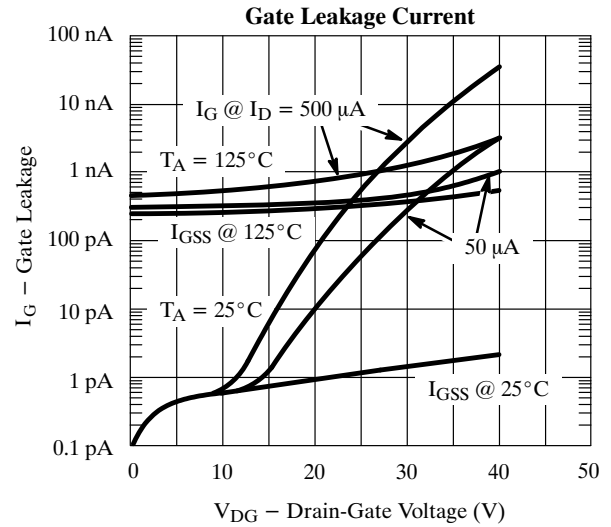
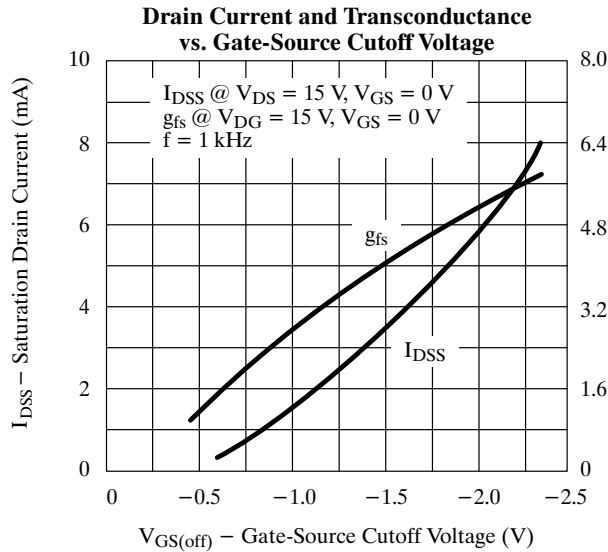
Parameter	Symbol	Test Conditions	Typ <sup>b</sup>	Limits						Unit
				U401		SST/U404		SST/U406		
				Min	Max	Min	Max	Min	Max	
<b>Static</b>										
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	$I_G = -1 \mu A, V_{DS} = 0 V$	-58	-40		-40		-40		V
	$V_{(BR)G1 - G2}$	$I_G = \pm 1 \mu A, V_{DS} = 0 V$ $V_{GS} = 0 V$	$\pm 45$	$\pm 30$		$\pm 30$		$\pm 30$		
Gate-Source Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 15 V, I_D = 1 nA$	-1.5	-0.5	-2.5	-0.5	-2.5	-0.5	-2.5	
Saturation Drain Current <sup>c</sup>	$I_{DSS}$	$V_{DS} = 10 V, V_{GS} = 0 V$	3.5	0.5	10	0.5	10	0.5	10	mA
Gate Reverse Current	$I_{GSS}$	$V_{GS} = -30 V, V_{DS} = 0 V$	-2		-25		-25		-25	pA
		$T_A = 125^\circ C$	-1							nA
Gate Operating Current	$I_G$	$V_{DG} = 15 V, I_D = 200 \mu A$	-2		-15		-15		-15	pA
		$T_A = 125^\circ C$	-0.8		-10		-10		-10	nA
Drain-Source On-Resistance	$r_{DS(on)}$	$V_{GS} = 0 V, I_D = 0.1 mA$	250							$\Omega$
Gate-Source Voltage	$V_{GS}$	$V_{DG} = 15 V, I_D = 200 \mu A$	-1		-2.3		-2.3		-2.3	V
Gate-Source Forward Voltage	$V_{GS(F)}$	$I_G = 1 mA, V_{DS} = 0 V$	0.7							
<b>Dynamic</b>										
Common-Source Forward Transconductance	$g_{fs}$	$V_{DS} = 15 V, I_D = 200 \mu A$ $f = 1 kHz$	1.5	1	2	1	2	1	2	mS
Common-Source Output Conductance	$g_{os}$		1.3		2		2		2	$\mu S$
Common-Source Forward Transconductance	$g_{fs}$	$V_{DS} = 10 V, V_{GS} = 0 V$ $f = 1 kHz$	4	2	7	2	7	2	7	mS
Common-Source Output Conductance	$g_{os}$		5		30		30		30	$\mu S$
Common-Source Input Capacitance	$C_{iss}$	$V_{DS} = 15 V, I_D = 200 \mu A$ $f = 1 MHz$	4		8		8		8	pF
Common-Source Reverse Transfer Capacitance	$C_{rss}$		1.5		3		3		3	
Equivalent Input Noise Voltage	$\bar{e}_n$	$V_{DS} = 15 V, I_D = 200 \mu A$ $f = 10 Hz$	10		20		20		20	$\frac{nV}{\sqrt{Hz}}$
<b>Matching</b>										
Differential Gate-Source Voltage	$ V_{GS1} - V_{GS2} $	$V_{DG} = 10 V, I_D = 200 \mu A$			5		15		40	mV
Gate-Source Voltage Differential Change with Temperature	$\frac{\Delta  V_{GS1} - V_{GS2} }{\Delta T}$	$V_{DG} = 10 V$ $I_D = 200 \mu A$ $T_A = -55 to 125^\circ C$	SST404	20						$\mu V/^\circ C$
			SST406	40						
			All U		10		25		80	
Common Mode Rejection Ratio	CMRR	$V_{DG} = 10 to 20 V, I_D = 200 \mu A$	102	95		95				dB

Notes

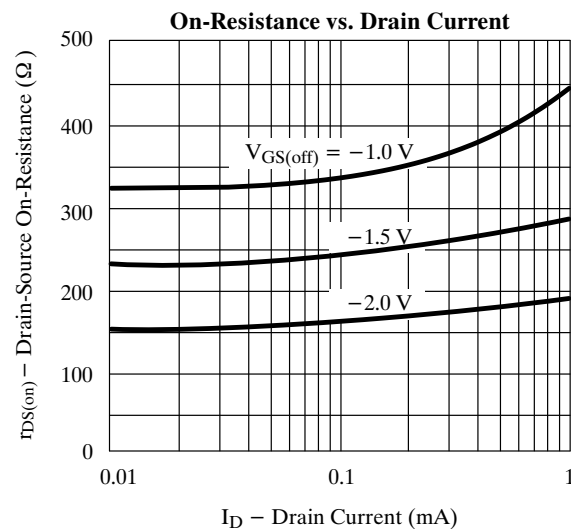
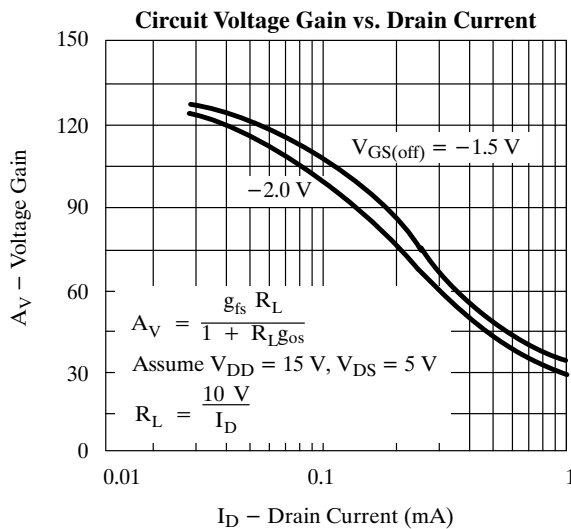
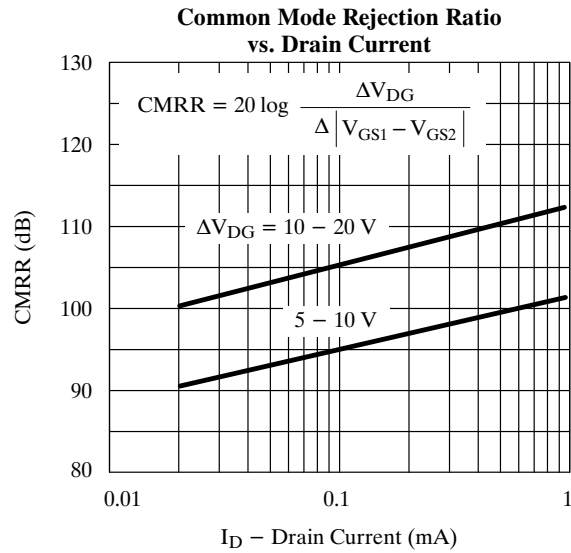
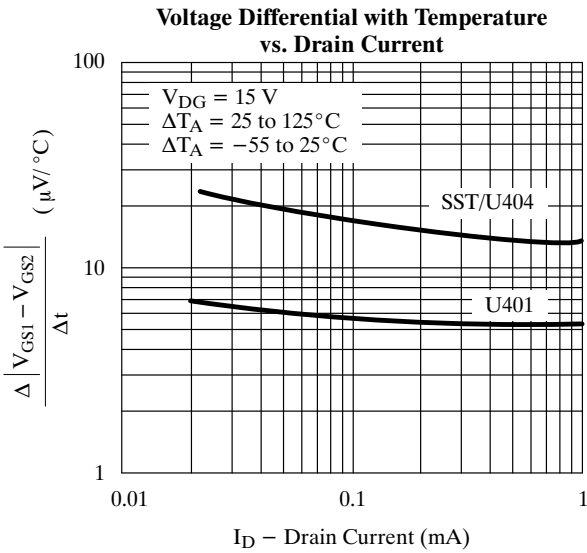
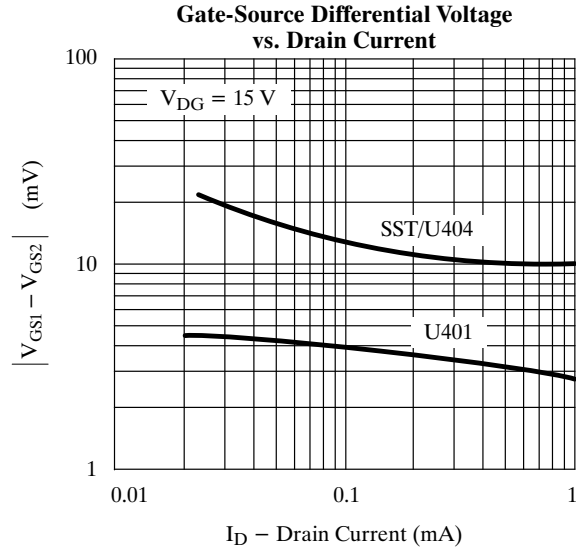
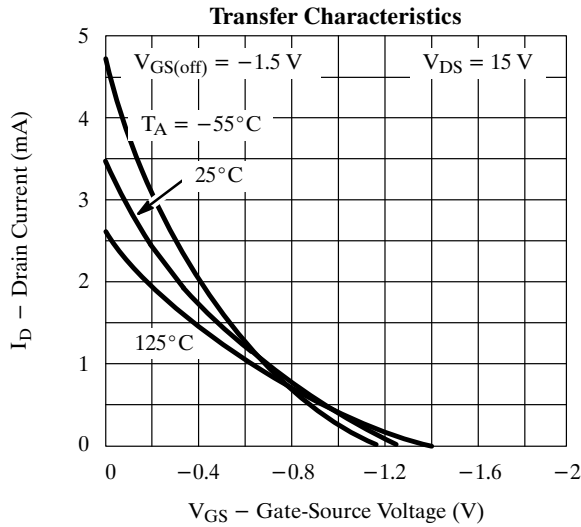
- $T_A = 25^\circ C$  unless otherwise noted.
- Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- Pulse test:  $PW \leq 300 \mu s$  duty cycle  $\leq 3\%$ .

NNR

## Typical Characteristics



### Typical Characteristics (Cont'd)



## Typical Characteristics (Cont'd)

